











SN74LVC1G125-Q1

ZHCSK63D - APRIL 2003 - REVISED AUGUST 2019

具有三杰输出的 SN74LVC1G125-Q1 单总线缓冲门

1 特性

- 符合 AEC-Q100 标准, 其中包括以下内容:
 - 器件温度 1 级: -40℃ 至 +125℃ 的环境运行温度范围
 - 器件人体放电模型 (HBM) ESD 分类等级 2
 - 器件带电器件模型 (CDM) ESD 分类等级 C5
- 采用具有 0.5mm 间距的小型 1.45mm² 封装 (DRY)
- 支持 5V V_{CC} 运行
- 过压容差输入最高可达 5.5V
- 支持向下转换到 V_{CC}
- 电压为 3.3V 时, t_{pd} 最大值为 3.7ns
- 低功耗, I_{CC} 最大值为 10μA
- 电压为 3.3V 时,输出驱动为 ±24mA
- loff 支持带电插入、局部关断模式和后驱动保护
- 闩锁性能超过 100mA, 符合 JESD 78 II 类规范

2 应用

- 符合汽车应用 应用
- 增加数字信号驱动强度
- 可转接驱动高达 100MHz 的方波信号
- 启用或禁用具有高阻抗关闭状态的数字信号

3 说明

此总线缓冲门专为 1.65V 至 5.5V V_{CC} 运行而设计。

SN74LVC1G125-Q1 器件是一款具有三态输出的单线驱动器。当输出使能 (OE) 输入为高电平时,输出被禁用。

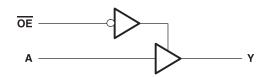
CMOS 器件具有高输出驱动,同时在宽 V_{CC} 工作范围内保持低静态功率耗散。

SN74LVC1G125-Q1 器件采用多种封装,包括外形尺寸为 1.45mm × 1.00mm 的小型 DRY 封装。

器件信息(1)

器件名称	封装	封装尺寸 (标称值)
1P1G125QDCKRQ1	SOT-23 (5)	2.90mm × 1.60mm
CLVC1G125QDBVRQ1	SC70 (5)	2.00mm x 1.25mm
1P1G125QDRYRQ1	SON (6)	1.45mm x 1.00mm

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附录。





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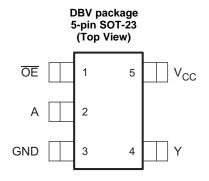
4 修订历史记录

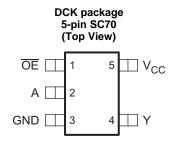
注: 之前版本的页码可能与当前版本有所不同。

CI	hanges from Revision C (April 2008) to Revision D	Page
•	已更改 根据新的 TI 标准更改了数据表格式	1
•	Added DRY package to Pin Configuration and Functions	3
•	Added Pin Functions table.	3
•	Added Handling Ratings table.	4
•	Added Thermal Information table.	5
•	Added –40°C to 125°C Temperature range to Electrical Characteristics	6
•	Added Detailed Description section.	10
•	Added Application and Implementation section.	11
•	Added Layout section.	12

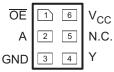


5 Pin Configuration and Functions





DRY package 6-pin SON (Transparent Top View)



N.C. – No internal connection

See mechanical drawings for dimensions.

Pin Functions

	PIN		I/O	DESCRIPTION
NAME	DBV, DCK	DRY	1/0	DESCRIPTION
ŌĒ	1	1	Input	Active low Output Enable Input
Α	2	2	Input	Input A
GND	3	3	_	Ground
Y	4	4	Output	Output Y
V _{CC}	5	6	_	Positive supply
NC	_	5	_	No internal connection



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range (2)		-0.5	6.5	V
Vo	Voltage range applied to any output in the high-impedance or power-off state (2)		-0.5	6.5	V
Vo	Voltage range applied to any output in th	e high or low state (2)(3)	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T_{J}	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V Floring state displayer	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level	±2000	V	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level	±1000	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating* table.



6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT	
,	Owner have the me	Operating	1.65	5.5		
/ _{cc}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
,	I Park Toward Samuel Control	V _{CC} = 2.3 V to 2.7 V	1.7			
V _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
.,	Law law Law Law at walka wa	V _{CC} = 2.3 V to 2.7 V		0.7	.,	
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V	
	V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}			
VI	Input voltage	•	0	5.5	V	
Vo	Output voltage		0	V _{CC}	V	
	V _{CC} = 1.65 V		-4			
		V _{CC} = 2.3 V		-8		
ОН	High-level output current	V _{CC} = 3 V		-16	mA	
				-24		
		V _{CC} = 4.5 V		-24		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8		
OL	Low-level output current	V 2 V		16	mA	
		V _{CC} = 3 V		24		
		V _{CC} = 4.5 V		24		
		V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20		
∆t/∆v	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
		V _{CC} = 5 V ± 0.5 V		5		
T _A	Operating free-air temperature		-40	125	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.4 Thermal Information

			SN74LVC1G125-Q1			
	THERMAL METRIC(1)	DBV	DCK	DRY	UNIT	
		5 PINS	5 PINS	6 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	229	278	439	°C/W	
R ₀ JC(top)	Junction-to-case (top) thermal resistance	164	93	277	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	62	65	271	°C/W	
ΨЈТ	Junction-to-top characterization parameter	44	2	84	°C/W	
ΨЈВ	Junction-to-board characterization parameter	62	64	271	°C/W	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	-	_	_	°C/W	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

			-40 °C	to 125 °C		
PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾ MAX	UNIT	
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			
N/	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		V	
V _{OH}	I _{OH} = -16 mA	3 V	2.4		\ \	
	1 24 24	3 V	2.3			
	$I_{OH} = -24 \text{ mA}$	4.5 V	3.8			
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1		
	I _{OL} = 4 mA	1.65 V		0.45		
V _{OL}	I _{OL} = 8 mA	2.3 V		0.3	V	
	I _{OL} = 16 mA	3 V		0.4		
		3 V		0.55		
	I _{OL} = 24 mA	4.5 V		0.55		
I _I A or \overline{OE} inputs	V _I = 5.5 V or GND	0 to 5.5 V		±5	μА	
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±10	μА	
l _{OZ}	$V_O = 0$ to 5.5 V			10	μΑ	
I _{CC}	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V		10	μΑ	
Δl _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V		500	μА	
C _I	V _I = V _{CC} or GND	3.3 V		4	pF	

⁽¹⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

6.6 Switching Characteristics

over recommended operating free-air temperature range of -40° C to 125° C, $C_L = 50$ pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 3. ± 0.3	3 V V	V _{CC} = 5 ± 0.5	5 V V	UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	1	5.1	1	4.1	ns
t _{en}	ŌĒ	Υ	1	6	1	5	ns
t _{dis}	ŌĒ	Υ	1	5	1	4.2	ns

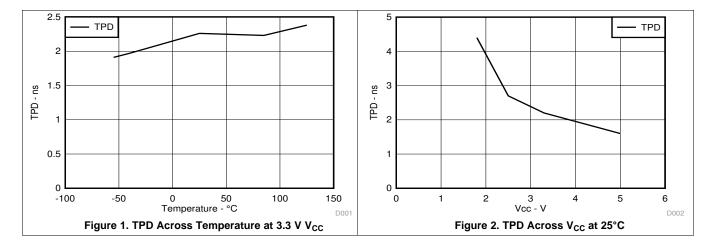
6.7 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETE	R	TEST CONDITIONS	V _{CC} = 3.3 V TYP	V _{CC} = 5 V TYP	UNIT
0	Power dissipation	Outputs enabled	f 40 MH=	19	21	, F
C _{pd}	capacitance	Outputs disabled	f = 10 MHz	2	4	p⊦

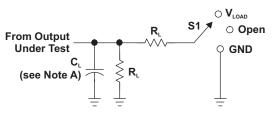


6.8 Typical Characteristics





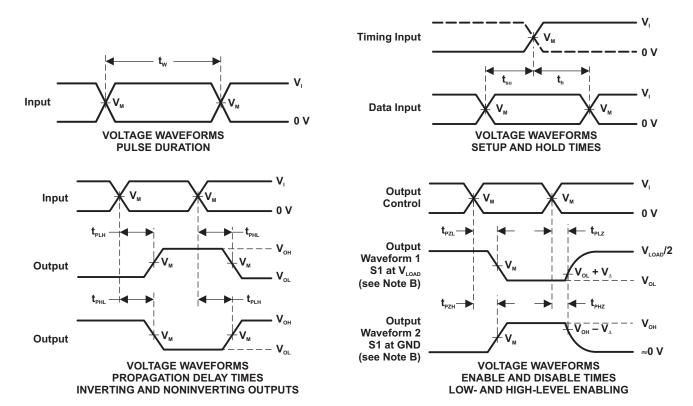
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INPUTS			v		-	V
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V



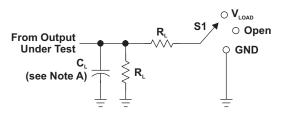
NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. t_{PlH} and t_{PHl} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms



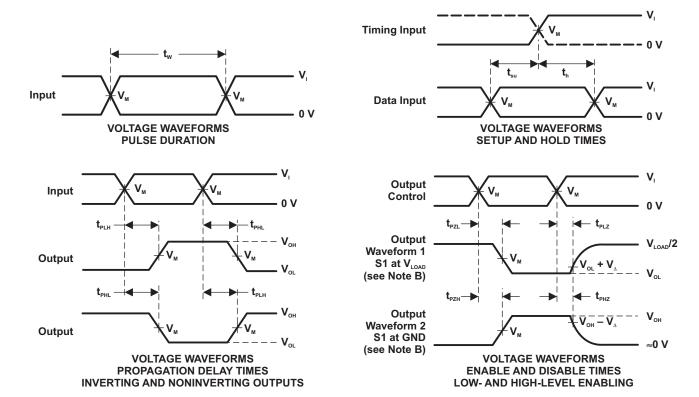
Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

,,	INPUTS			V		-	.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	$V_{\scriptscriptstyle{\Delta}}$
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
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- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms



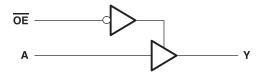
8 Detailed Description

8.1 Overview

The SN74LVC1G125-Q1 device contains one buffer gate device with output enable control and performs the Boolean function Y = A. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating voltage range
 - Operates from 1.65 V to 5.5 V
- Allows down voltage translation
- Inputs accept voltages to 5.5 V
- I_{off} feature allows voltages on the inputs and outputs, when V_{CC} is 0 V

8.4 Device Functional Modes

Table 1. Function Table

INP	UTS	OUTPUT
ŌĒ	Α	Υ
L	Н	Н
L	L	L
Н	X	Z



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G125-Q1 device is a high drive CMOS device that can be used as a output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to $V_{\rm CC}$.

9.2 Typical Application

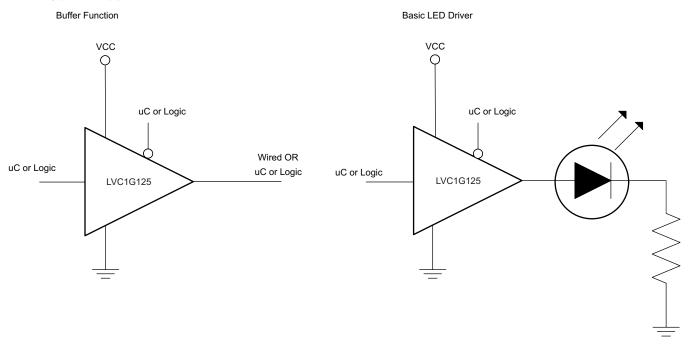


Figure 5. Typical Application Schematic

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{II}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

2. Recommend Output Conditions

Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.



Typical Application (continued)

Outputs should not be pulled above V_{CC}.

9.2.3 Application Curves

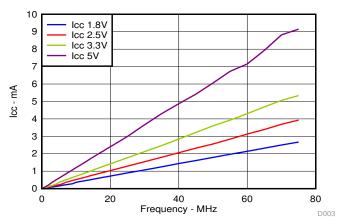


Figure 6. I_{CC} vs Frequency, Square wave input signal

10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a 0.1- μ F capacitor is recommended and if there are multiple VCC pins then a 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Figure 7 shows the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

11.2 Layout Example



Figure 7. Package Layout



12 器件和文档支持

12.1 接收文档更新通知

要接收文档更新通知,请导航至 ti.com. 上的器件产品文件夹。单击右上角的通知我进行注册,即可每周接收产品 信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

12.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 商标

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All other trademarks are the property of their respective owners.

静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序,可 能会损坏集成电路。



ESD 的损坏小至导致微小的性能降级,大至整个器件故障。 精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可 能会导致器件与其发布的规格不相符。

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且 不会对此文档进行修订。如需获取此数据表的浏览器版本,请查阅左侧的导航栏。

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10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
1P1G125QDCKRG4Q1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CMR	Samples
1P1G125QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CMR	Samples
1P1G125QDRYRQ1	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	FX	Samples
CLVC1G125QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25O	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

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PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2021

TAPE AND REEL INFORMATION





Α0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
1P1G125QDCKRQ1	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
1P1G125QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1
CLVC1G125QDBVRQ1	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

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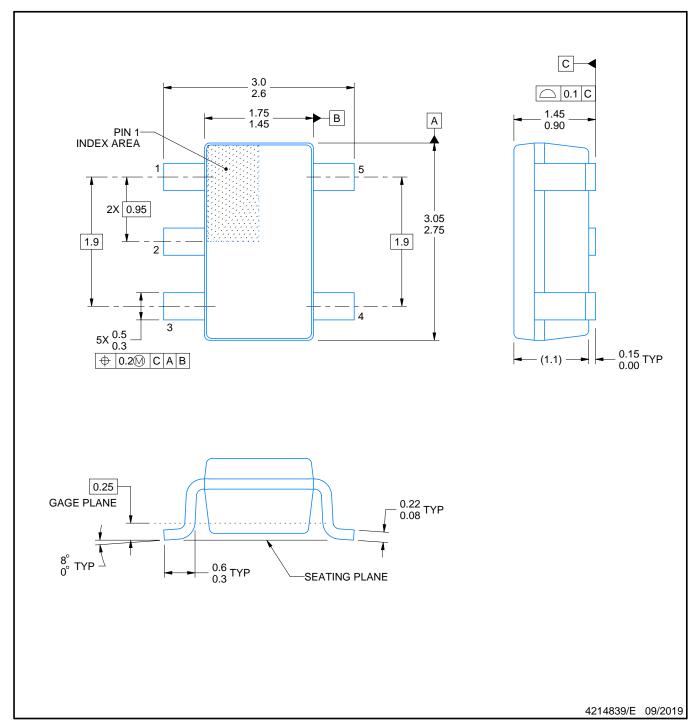


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
1P1G125QDCKRQ1	SC70	DCK	5	3000	202.0	201.0	28.0
1P1G125QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0
CLVC1G125QDBVRQ1	SOT-23	DBV	5	3000	200.0	183.0	25.0



SMALL OUTLINE TRANSISTOR



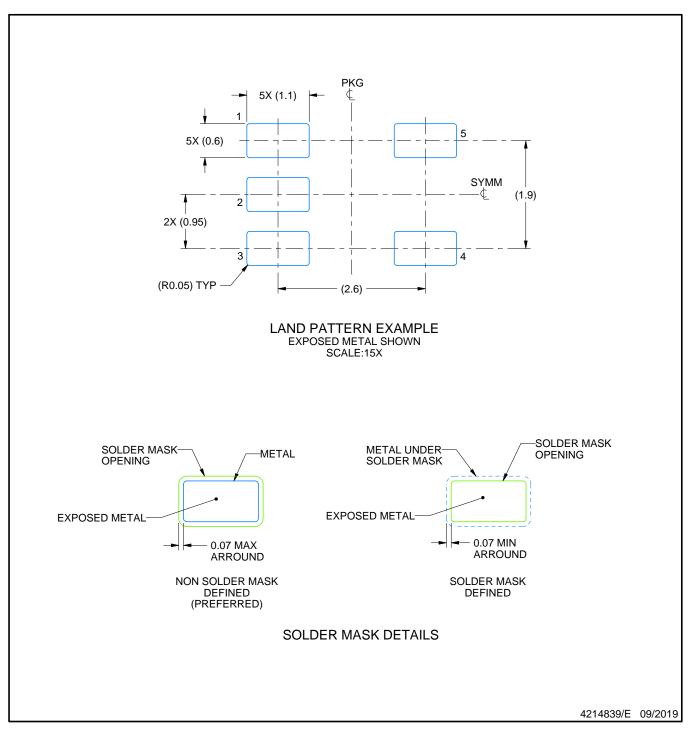
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



SMALL OUTLINE TRANSISTOR



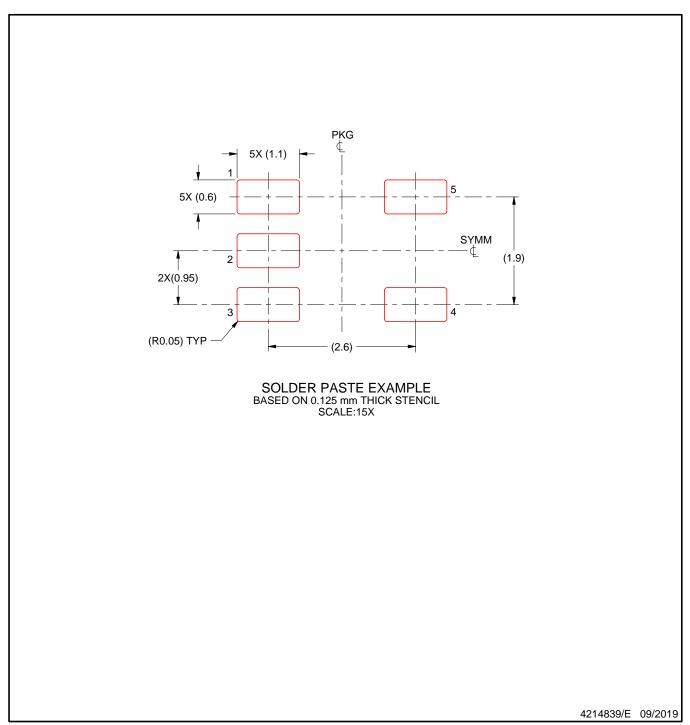
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





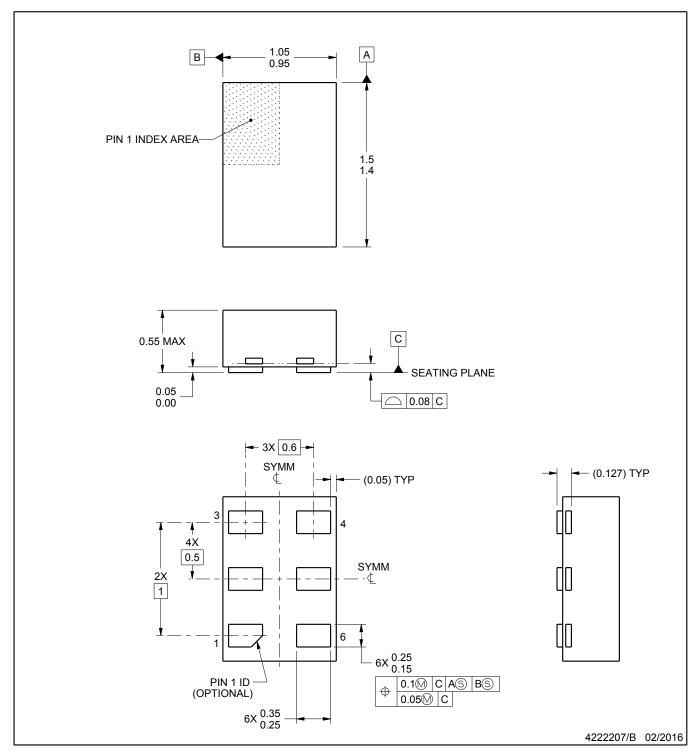
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC SMALL OUTLINE - NO LEAD



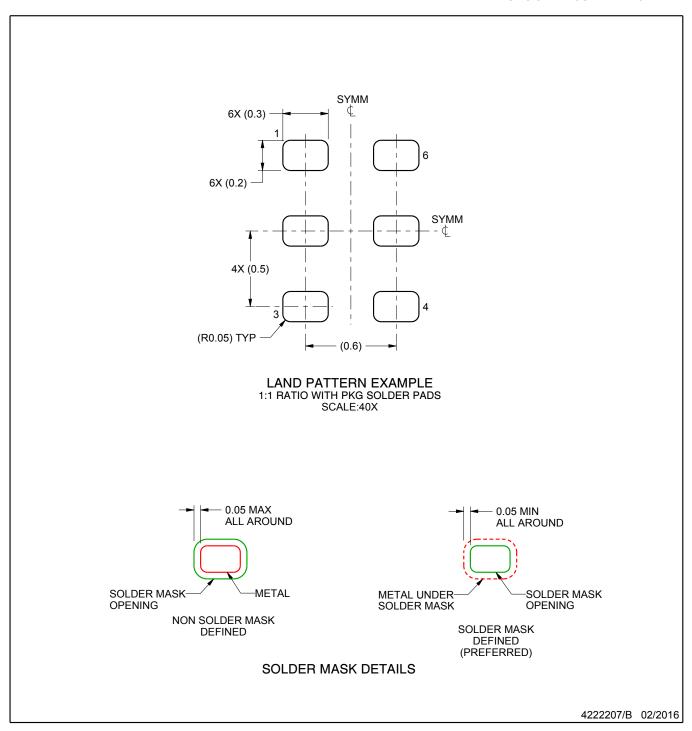
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD

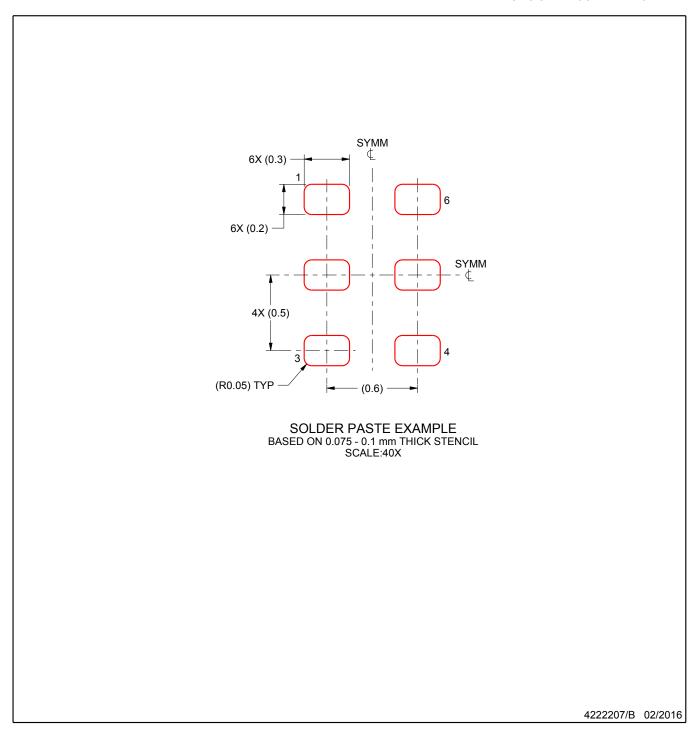


NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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